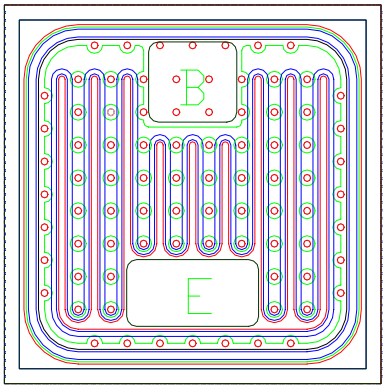
A1020 Silicon PNP Epitaxial Transistor

Description: The A1020 is designed for use in power amplifier applications and power switching applications

Features: ●Low collector saturation voltage

●Complementary to C2328

Chip Appearance



Chip Size		760um×760um
Chip Thickness		210±20um
Bonding Pad Size	Base	160×170um
	Emitter	130×260um
Front Metal		Al
Backside Metal		Au
Scribe line width		60um
Wafer Size		6 inch

Electrical Characteristics(Ta=25℃)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB}=-35V, I_E=0		-0.1	uA
Emitter Cutoff Current	I_{EBO}	V_{EB}=-5V, I_C=0		-0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=-0.1mA	-40		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=-10mA	-30		V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=-0.1mA	-5.0		V
DC Current Gain	h_{FE}	V_{CE}=-2V, I_C=-0.5A	80	400	
Collector Saturation Voltage	$V_{CE(sat)}$	I_C=-1A, I_B=-50mA		-0.5	V